1. (Previously Presented) A protection circuit for an integrated circuit device that includes silicon over insulator (SOI) transistors, wherein said protection circuit comprises:

a shunt connected to at least one of the source/drain and gate of at least one SOI transistor; and

a compensating conductor connected to said shunt,

wherein said shunt and said compensating conductor eliminate the potential for charging damage to the gate insulator of said SOI transistor, and

wherein said shunt and said compensating conductor perform no function other than eliminating said potential for charging damage.

2. (Original) The circuit in claim 1, wherein said shunt device is positioned in parallel with said SOI transistor.

3. (Original) The circuit in claim 1, wherein said shunt device is positioned between a first conductor connected to said source/drain of said SOI transistor and a second conductor connected to said gate of said SOI transistor.

4. (Original) The circuit in claim 1, further comprising a series device in place of said shunt.

5. (Original) The circuit in claim 4, wherein said series device is positioned between a first conductor connected to said SOI transistor and a second conductor that is not connected to said SOI transistor.

6. (Original) The circuit in claim 4, further comprising a second series device, wherein said series device is connected to a first conductor and said second series device is connected to a second conductor, and

wherein said first conductor is connected to said source/drain of said SOI transistor and said second conductor is connected to said gate of said SOI transistor.

7. (Previously Presented) A protection circuit for an integrated circuit device that includes silicon over insulator (SOI) transistors, wherein said protection circuit comprises:

a series device connected to at least one of the source/drain and gate of at least one SOI transistor; and

a compensating conductor connected to said series device,

wherein said series device and said compensating conductor eliminate the potential for charging damage between said source/drain and said gate of said SOI transistor, and

wherein said series device and said compensating conductor perform no function other than eliminating said potential for charging damage.

8. (Original) The circuit in claim 7, wherein said series device is positioned in parallel with said SOI transistor.

9. (Original) The circuit in claim 7, wherein said series device is positioned between a first conductor connected to said source/drain of said SOI transistor and a second conductor connected to said gate of said SOI transistor.

10. (Original) The circuit in claim 7, wherein said series device comprises a diode.

11. (Original) The circuit in claim 7, wherein said series device is positioned between a first conductor connected to said SOI transistor and a second conductor that is not connected to said SOI transistor.

12. (Original) The circuit in claim 7, further comprising a second series device, wherein said series device is connected to a first conductor and said second series device is connected to a second conductor, and

wherein said first conductor is connected to said source/drain of said SOI transistor and said second conductor is connected to said gate of said SOI transistor.

13-36 (Canceled).

37. (Previously Presented) A protection circuit for an integrated circuit device that includes silicon over insulator (SOI) transistors, wherein said protection circuit comprises:

a shunt connected to at least one of the source/drain and gate of at least one SOI transistor; and

a first compensating conductor connected to said shunt;

a series device connected to at least one of the source/drain and gate of at least one SOI transistor, wherein said shunt and said series device are connected to different features of said at least one SOI transistor; and

a second compensating conductor connected to said series device,

wherein said shunt, said series device, said first compensating conductor, and said second compensating conductor eliminate the potential for charging damage to the gate insulator of said SOI transistor, and

wherein said shunt, said series device, said first compensating conductor, and said second compensating conductor perform no function other than eliminating said potential for charging damage.

38. (Previously Presented) The circuit in claim 37, wherein said shunt device is positioned in parallel with said SOI transistor.

39. (Previously Presented) The circuit in claim 37, wherein said shunt device is positioned between a third conductor connected to said SOI transistor and said first compensating conductor that is not connected to said SOI transistor.

40. (Previously Presented )The circuit in claim 37, wherein said series device is positioned between a third conductor connected to said SOI transistor and said second compensating conductor that is not connected to said SOI transistor.